2SA2166

FOR GENERAL PURPOSE HIGH CURRENT DRIVE APPLICATION
SILICON PNP EPITAXIAL TYPE

DESCRIPTION

ISAHAYA 2SA2166 is a silicon PNP epitaxial type transistor designed with high collector current, low $V_{CE(sat)}$.

FEATURE

●High collector current

$I_{C(MAX)}$=−500mA

●Low collector to emitter saturation voltage

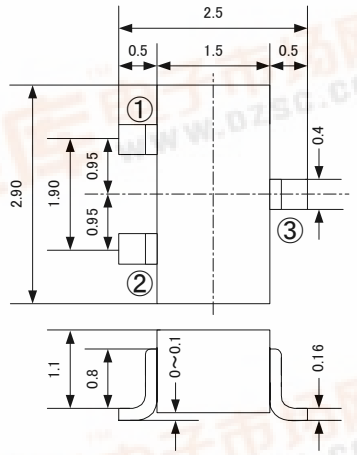
$V_{CE(sat)}$<−0.4V_{max}(IC=−150mA、IB=−15mA)

APPLICATION

For switching application, small type motor drive application.

OUTLINE DRAWING

Unit:mm



Notice: **The dimension without tolerance represent central value.**

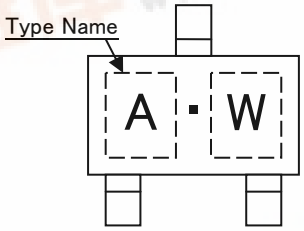
TERMINAL CONNECTOR

①:BASE EIAJ:SC-59

②:EMITTER JEDEC:TO-236

③:COLLECTOR Resemblance

MARKING



MAXIMUM RATINGS(Ta=25℃)

記 号	項 目	定 格 値	単 位
V_{CEO}	Collector to Emitter voltage	−60	V
V_{CBO}	Collector to Base voltage	−60	V
V_{EBO}	Emitter to Base voltage	−5	V
I_C	Collector current	−500	mA
P_C	Collector dissipation	200	mW
T_j	Junction temperature	150	℃
T_{stg}	Storage temperature	−55～150	℃

ELECTRICAL CHARACTERISTICS(Ta=25℃)

Symbol	Parameter	Test condition	Limits			Unit
			Min	Typ	Max	
$V_{(BR)CEO}$	C to E break down voltage	IC=−1mA、IB=0	−60			V
$V_{(BR)CBO}$	C to B break down voltage	IC=−10uA、IE=0	−60			V
$V_{(BR)EBO}$	E to B break down voltage	IE=−10uA、IC=0	−5			V
I_{CBO}	Collector cut off current	VCB=−50V、IE=0			−100	nA
I_{EBO}	Emitter cut off current	VEB=−3V、IC=0			−100	nA
h_{FE}	DC forward current gain	IC=−150mA、VCE=−10V	100		300	----
$V_{CE(sat)}$	C to E saturation voltage	IC=−150mA、IB=−15mA			−0.4	V
$V_{BE(sat)}$	B to E saturation voltage	IC=−150mA、IB=−15mA			−1.3	V
f_T	Gain band width product	IE=50mA、VCE=−20V、f=100MHz	200			MHz
C_{ob}	Collector output capacitance	VCB=−10V、f=1MHz			8	pF

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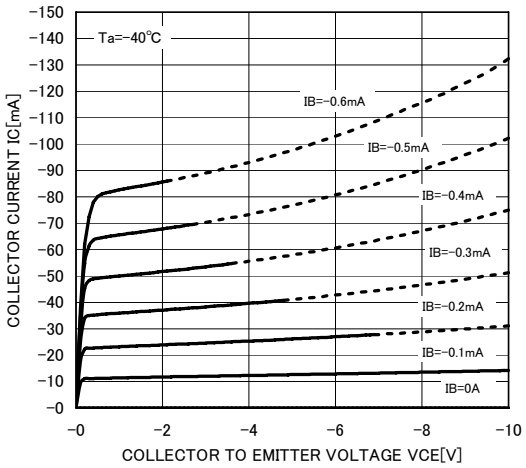
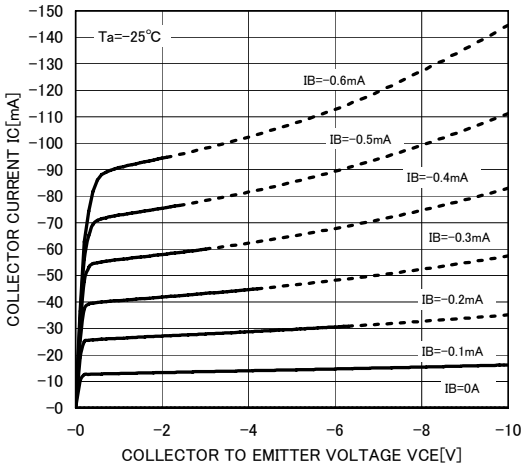
TYPICAL CHARACTERISTICS

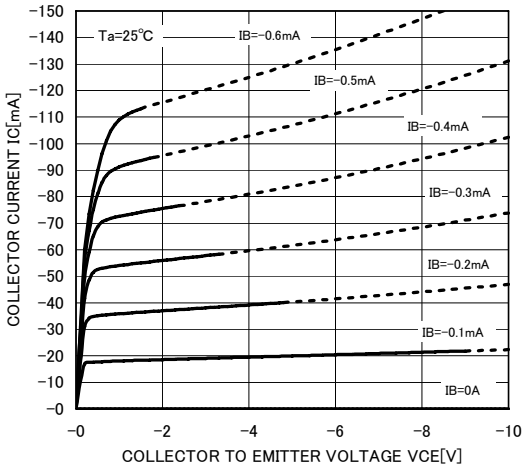
COMMON EMITTER OUTPUT



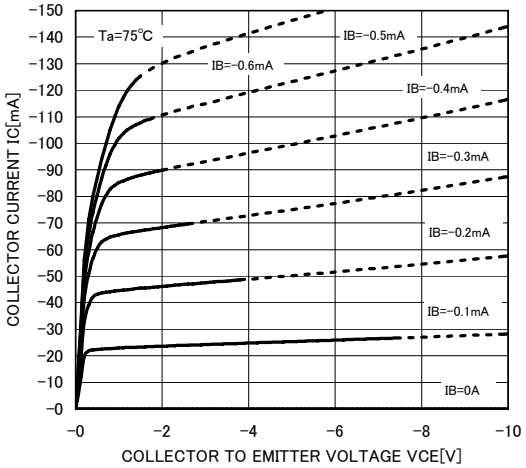
COMMON EMITTER OUTPUT



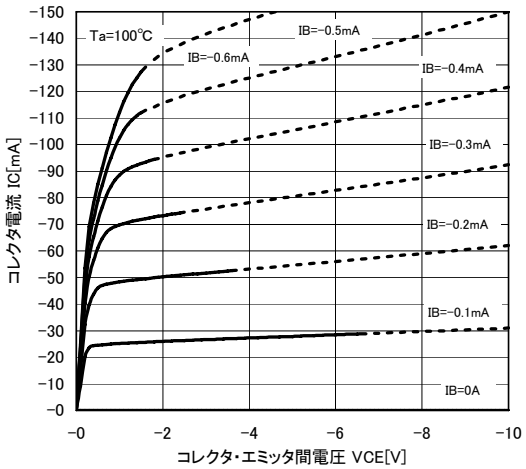
COMMON EMITTER OUTPUT



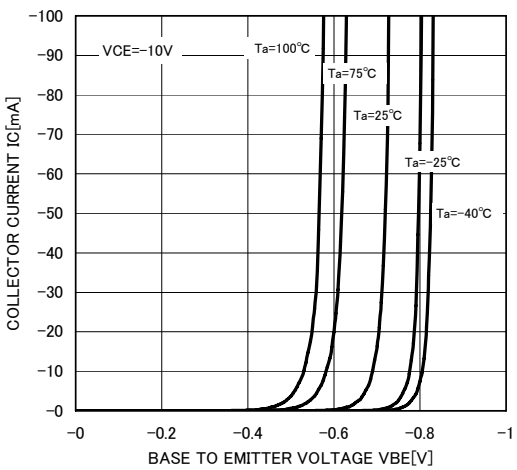
COMMON EMITTER OUTPUT



エミッタ接地出力特性



COMMON EMITTER TRANSFER



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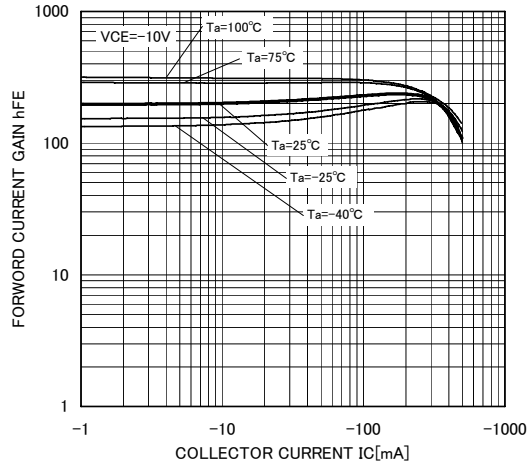
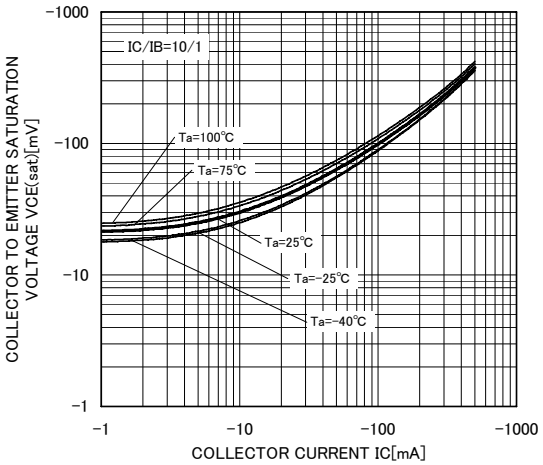
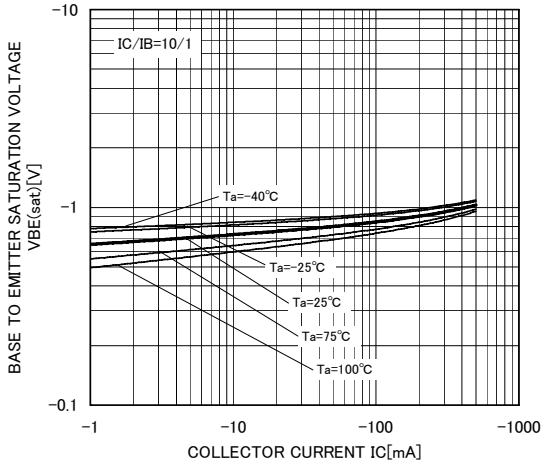
DC FORWORD CURRENT GAIN
VS. COLLECTOR CURRENT



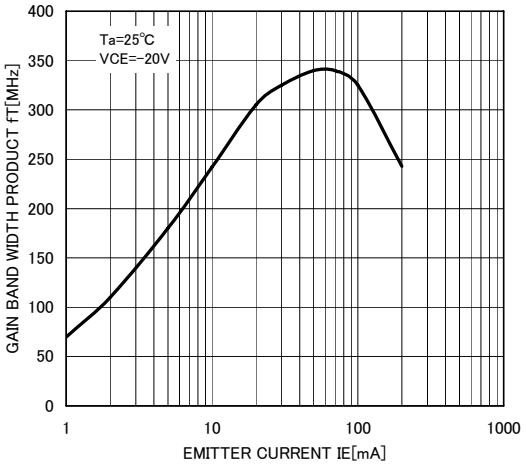
COLLECTOR TO EMITTER SATURATION VOLTAGE
VS. COLLECTOR CURRENT



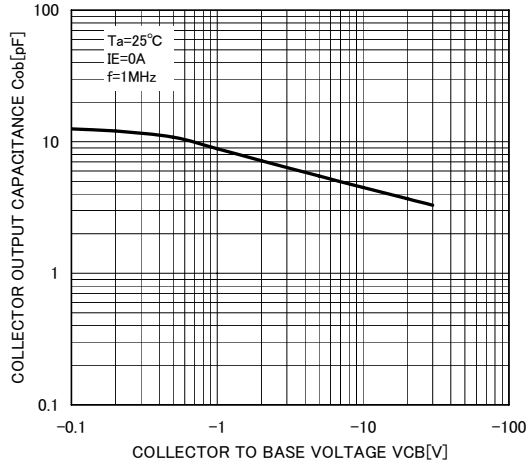
BASE TO EMITTER SATURATION VOLTAGE
VS. COLLECTOR CURRENT



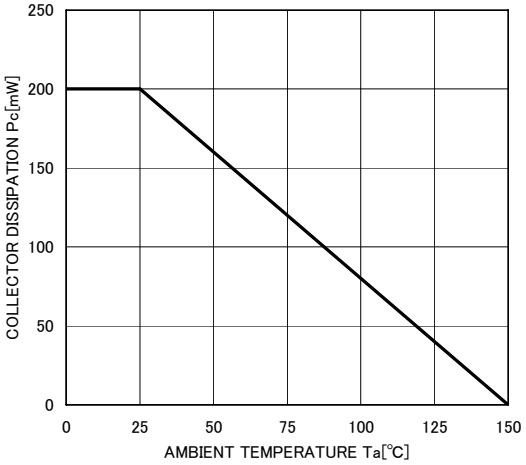
GAIN BAND WIDTH PRODUCT
VS. EMITTER CURRENT



COLLECTOR OUTPUT CAPATITANCE
VS. COLLECTOR TO BASE VOLTAGE



COLLECTOR DISSIPATION
VS. AMBIENT TEMPERATURE



ISAHAYA ELECTRONICS CORPORATION

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